SPECIFICATION

REFOND P/N

RF-817

■R&D

□Mass Product

Contents

1.Features

(1) Current transfer ratio (CTR : MIN. 50% at IF = 5mA, VCE = 5V)
(2) High input-output isolation voltage (Viso = 5,000Vrms)
(3) Response time (tr : TYP. 4μs at VCE = 2V, IC = 2mA, RL = 100Ω)

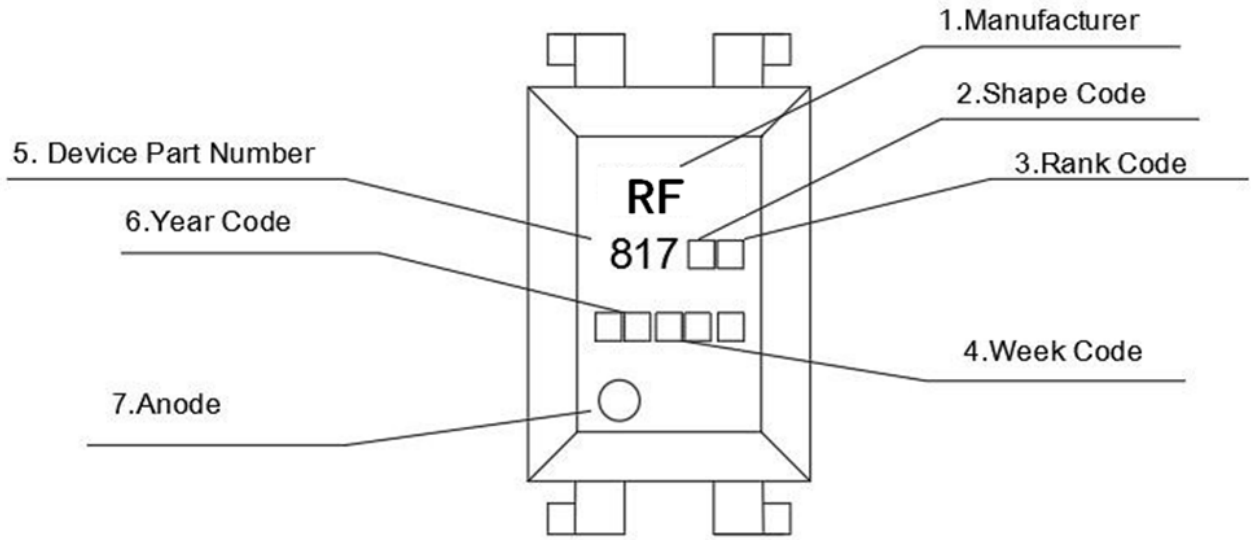
2.Description

(1) RF-817 photocoupler consist of one piece of GaAs emitter and one piece of NPN transistor.
(2) They are packaged in a 4-pin DIP package and available in wide-lead spacing and SMD option.

3.Applications

(1) Computer terminals.
(2) System appliances, measuring instruments.
(3) Registers, copiers, automatic vending machines.
(4) Electric home appliances, such as fan heaters, etc.
(5) Signal transmission between circuits of different potentials and impedances.

4.Naming Rule



(1) RF denotes REFOND.

(2) □denotes Shape Code.

(3) □□denotes Rank code.

(4) □□denotes Week code.

(5) □□denotes Device Part Number.

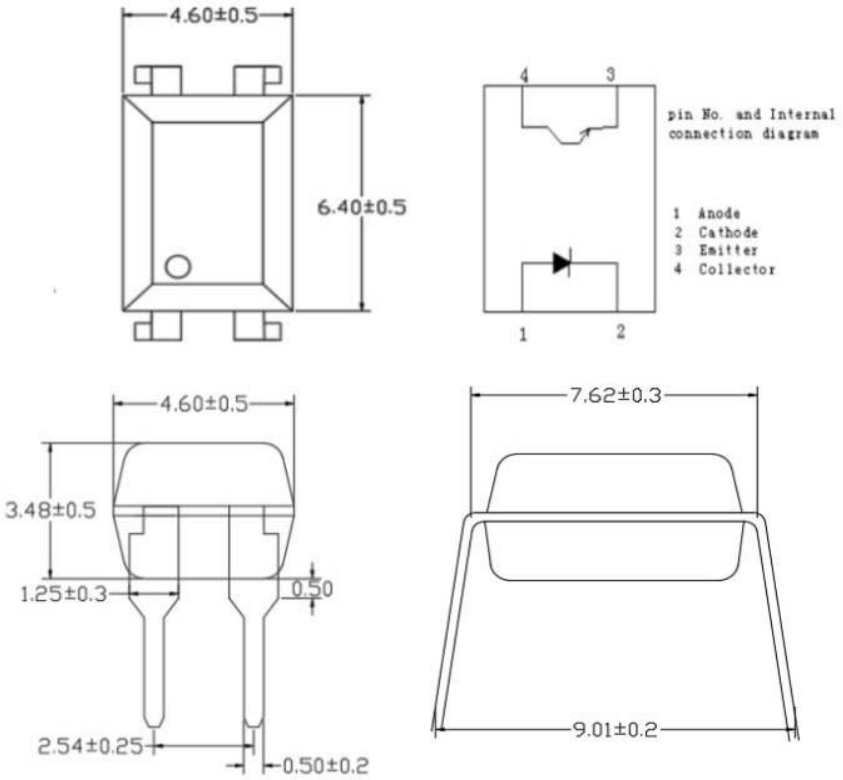
(6) □detes Year Code.

(7) Anode.

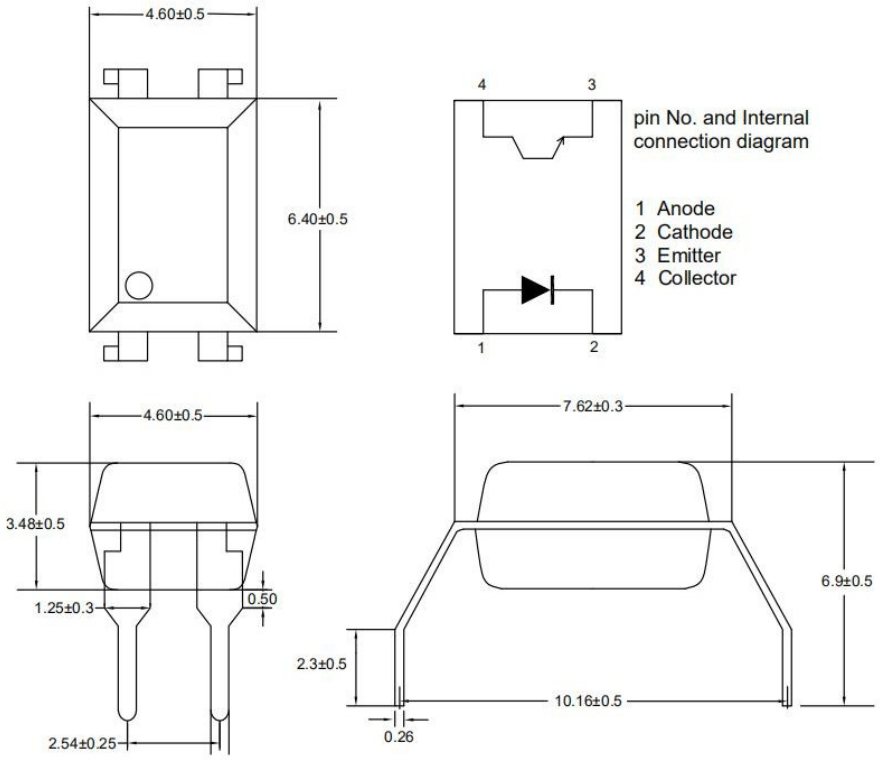
(8) Unit:mm

5.Package Dimension (Unit：mm）

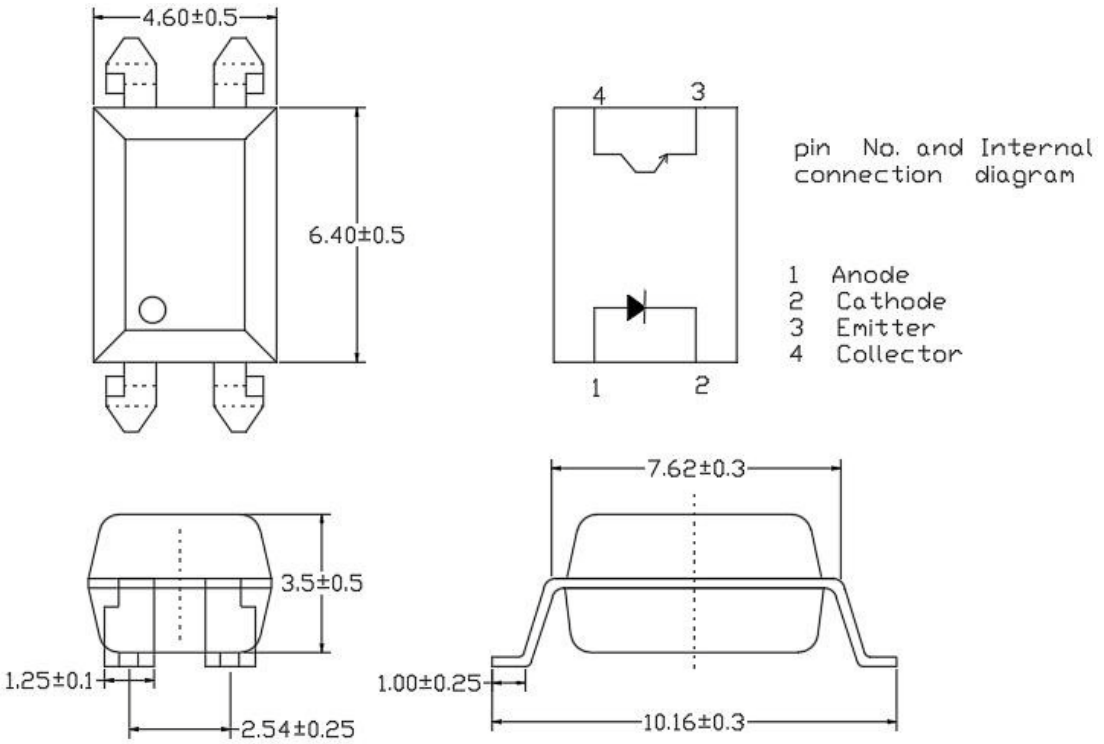
(1) RF-817



(2) RF-817M

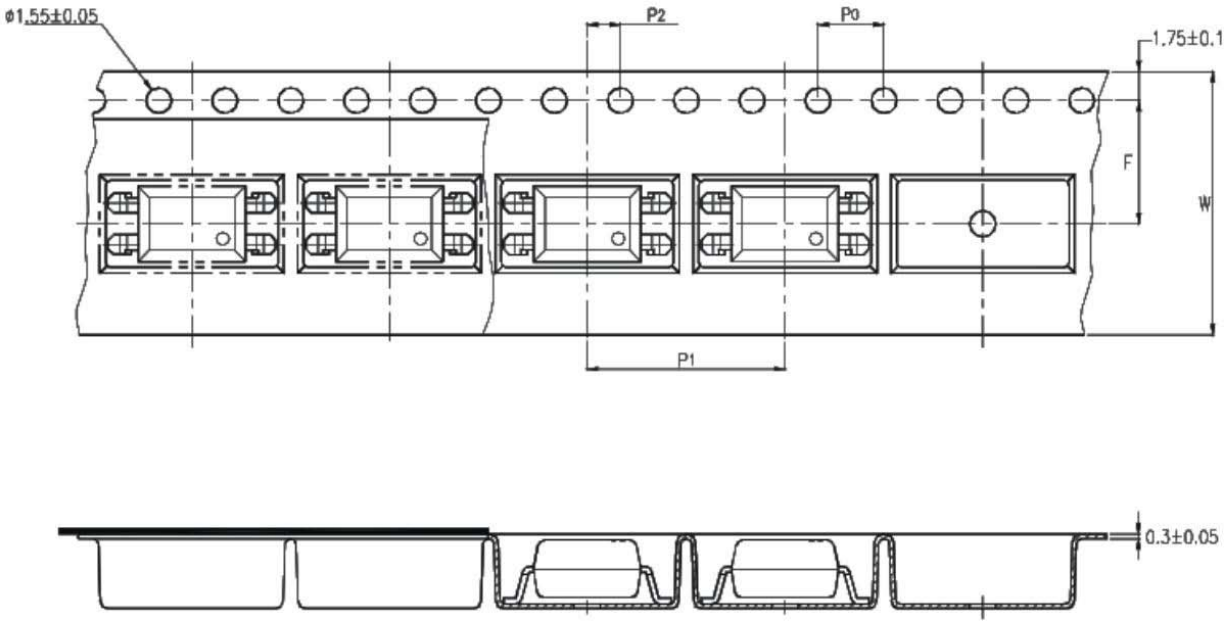


(3) RF-817S

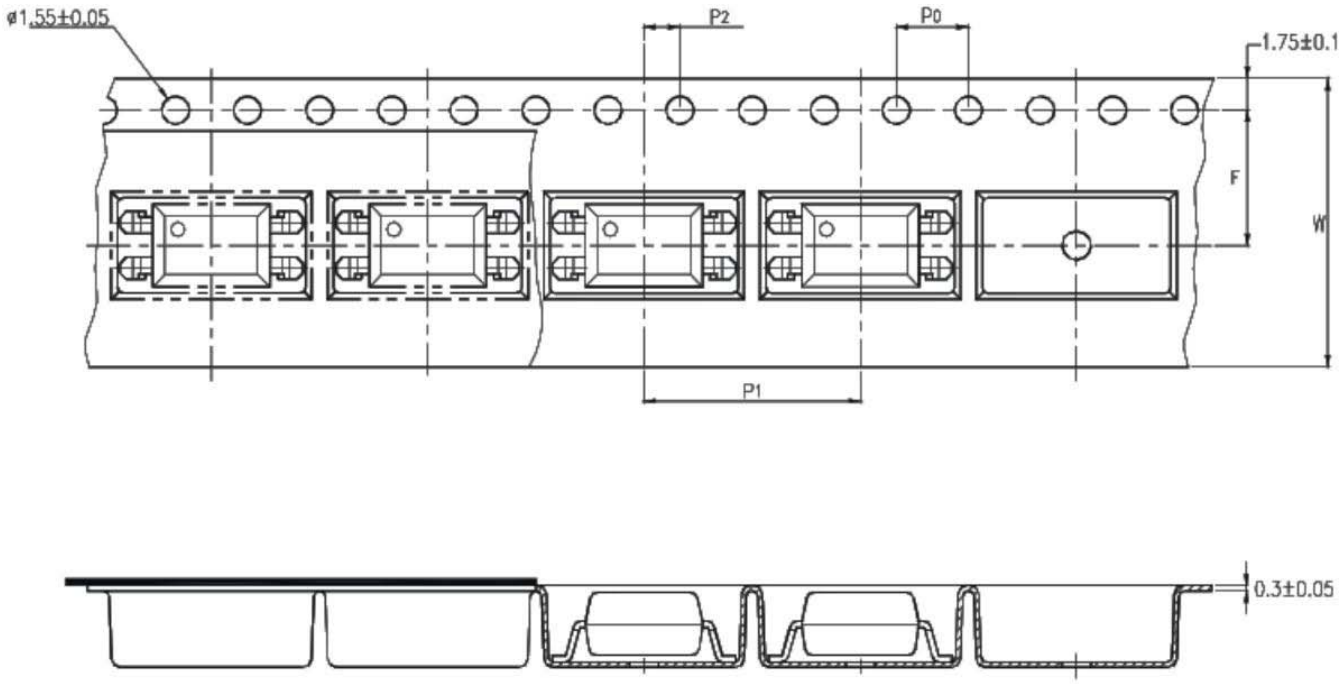


6.Taping Dimensions

(1) RF-817S-TA



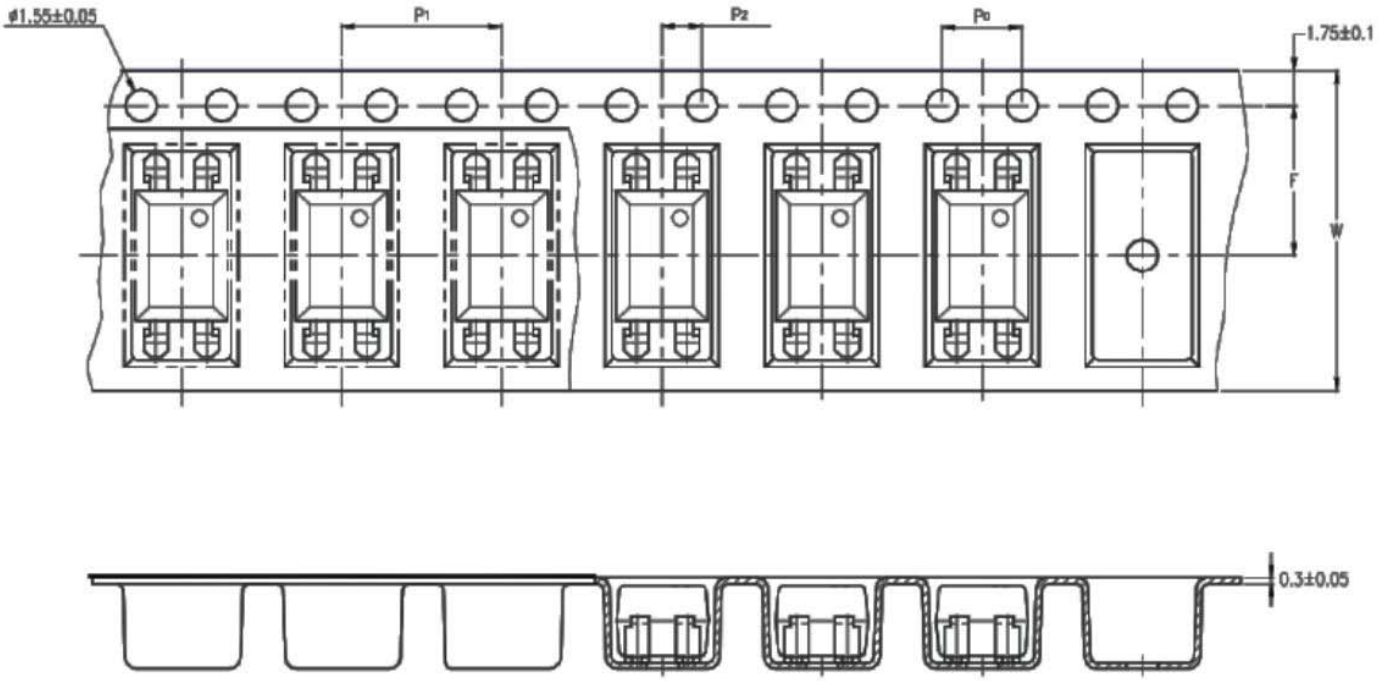
(2) RF-817S-TA1



Description	Symbol	Dimension in mm (inch)
Tape wide	W	16±0.3 (.63)
Pitch of sprocket holes	P_0	4±0.1 (.15)
Distance of compartment	F	7.5±0.1 (.295)
	P2	2±0.1 (.0079)
Distance of compartment to compartment	P1	12±0.1 (.472)

Package Type	TA/TA1
Quantities(pcs)	1000

(3) RF-817S-TP



Description	Symbol	Dimension in mm (inch)
Tape wide	W	16±0.3 (.63)
Pitch of sprocket holes	P_0	4±0.1 (.15)
Distance of compartment	F	7.5±0.1 (.295)
	P2	2±0.1 (.0079)
Distance of compartment to compartment	P1	8±0.1 (.472)

Package Type	TP
Quantities(pcs)	2000

7.Absolute Maximum Ratings at Ta=25℃

Parameter		Symbol	Rated Value	Unit
Input	Forward Current	I_F	60	mA
	Peak forward current (100μs pulse, 100Hz frequency)	I_{FP}	1	A
	Reverse Voltage	V_R	6	V
	Consume Power	P	70	mW
Output	Collector and emitter Voltage	V_{CEO}	80	V
	Emitter and collector Voltage	V_{ECO}	7	
	Collector Current	I_C	50	mA
	Consume Power	P_C	150	mW
Total Consume Power		P_{tot}	200	mW
*1 Insulation Voltage		V_{iso}	5,000	Vrms
Max Insulation Voltage (Insulating oil test)		VIOTM	10,000	V
Rated Impulse Insulation Voltage		VIORM	630	V
Working Temperature		Topr	-55 to + 110	℃
Deposit Temperature		T_{stg}	-55 to + 125	
*2 Soldering Temperature		T_{sol}	260	

*1.AC For 1 Minute, R.H. = 40 ~ 60%.

Isolation voltage shall be measured using the following method.

①Short between anode and cathode on the primary side and between collector and emitter on the secondary side.

②The isolation voltage tester with zero-cross circuit shall be used.

③The waveform of applied voltage shall be a sine wave.

*2.Soldering time is 10seconds.

8.Electro-Optical Characteristics (Ta=25℃ unless specified otherwise)

Parameter		Symbol	Condition	Min	Typ.*	Max	Unit
Input	Forward Current	V_F	I_F=20mA	---	1.2	1.4	V
	Reverse Voltage	I_R	V_R=4V	---	---	10	μA
	Collector capacitance	C_t	V=0, f=1KHz	---	30	250	pF
Output	Collector to emitter Current	I_{CEO}	V_{CE}=20V, I_F=0mA	---	---	100	nA
	Collector and Emitter attenuation Voltage	BV_{CEO}	I_C=0.1mA I_F=0mA	80	---	---	V
	Emitter and Collector attenuation Voltage	BV_{ECO}	I_E=0.01mA I_F=0mA	7	---	---	V
Transforming Characteristics	*1 Current conversion ratio	CTR	IF=5mA VCE=5V	50	---	1000	%
	Collector Current	I_C		2.5	---	50	mA
	Collector and Emitter Saturation Voltage	$V_{CE(sat)}$	I_F=20mA I_C=1mA	---	0.1	0.2	V
	Insulation Impedance	R_{iso}	DC500V 40~60%R.H.	---	1×10^{12}	---	Ω
	Floating Capacitance	C_f	V=0, f=1MHz	---	0.6	1.0	pF
	Cut-off Frequency	f_c	V_{CE}=5V, I_C=2mA R_L=100Ω, -3dB	---	80	---	kHz
	Rise Time	t_r	V_{CE}=2V, I_C=2mA R_L=100Ω	---	4	18	μs
	Descend Time	t_f		---	3	18	μs

*1 Current Conversion Ratio = I_C / I_F × 100% , CTRTolerance:±3%.

9.Rank Table of Current Transfer Ratio

Grade Sign	Min (%)	Max(%)
RF-817A	80	160
RF-817B	130	260
RF-817C	200	400
RF-817D	300	600

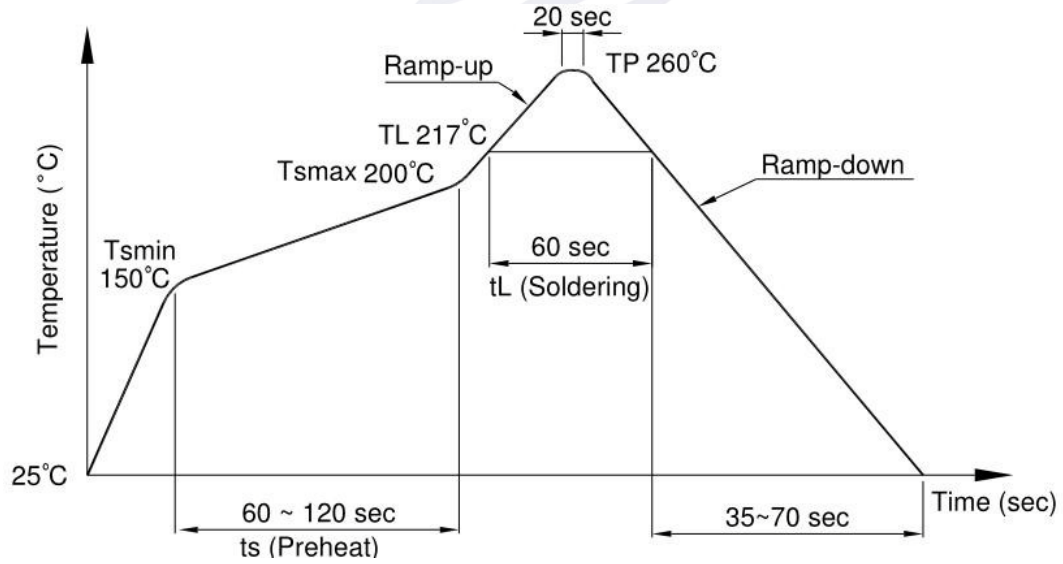
Note: Working condition: IF=5mA, VCE=5V, Ta=25℃.

10.Temperature Profile Of Soldering

(1).IR Reflow soldering (JEDEC-STD-020C compliant)

One time soldering reflow is recommended within the condition of temperature and time profile shown below. Do not solder more than three times.

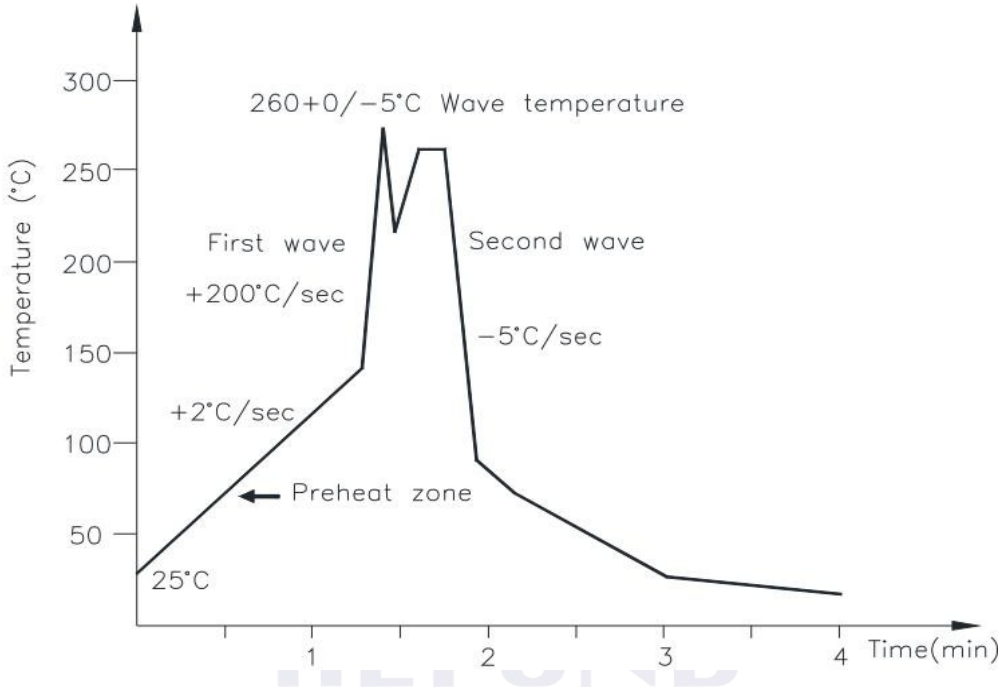
Profile item	Conditions
Preheat - Temperature Min (T_{Smin}) - Temperature Max (T_{Smax}) - Time (min to max) (ts)	150˚C 200˚C 90±30 sec
Soldering zone - Temperature (TL) - Time (t_L)	217˚C 60sec
Peak Temperature(T_P)	260˚C
Ramp-up rate	3˚C / sec max.
Ramp-down rate	3~6˚C / sec



(2).Wave soldering (JEDEC22A111 compliant)

One time soldering is recommended within the condition of temperature.

Temperature Time	260+0/-5˚C 10 sec
Preheat temperature Preheat time	25 to140˚C 30 to 80sec



(3).Hand soldering by soldering iron

Allow single lead soldering in every single process. One time soldering is recommended.

Temperature Time	380+0/-5˚C 3 sec max

11.Characteristics Curves

Fig.1 Forword Current vs. Ambient Temperatute

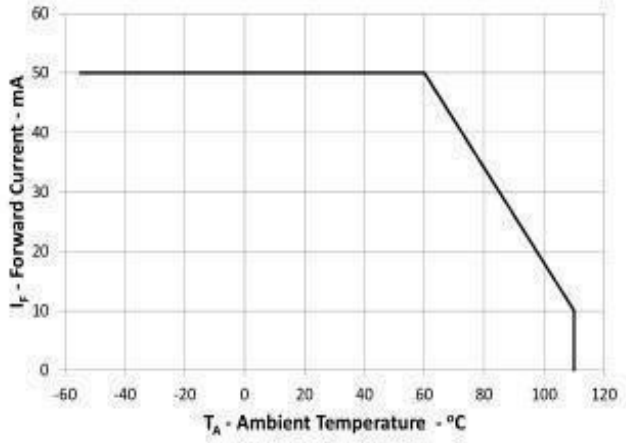


Fig.2 Collector Power Dissiption vs. Ambient Temperature

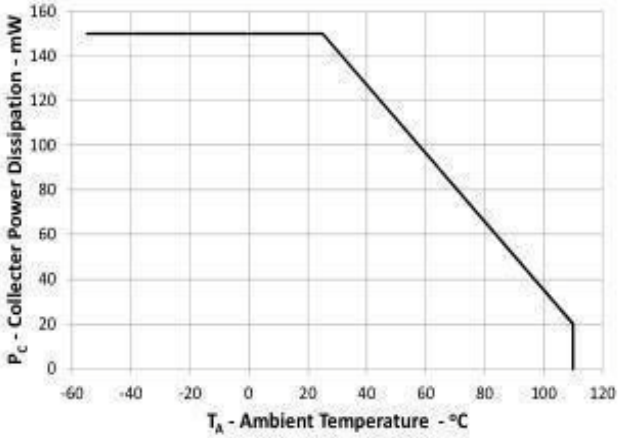


Fig.3 Collector-emitter Saturation Voltage vs. Forward Current

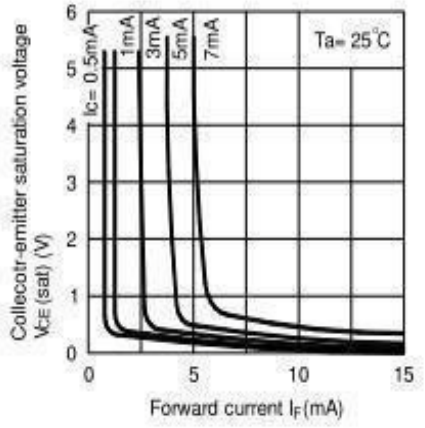


Fig.4 Forward Current vs. Forward Voltage

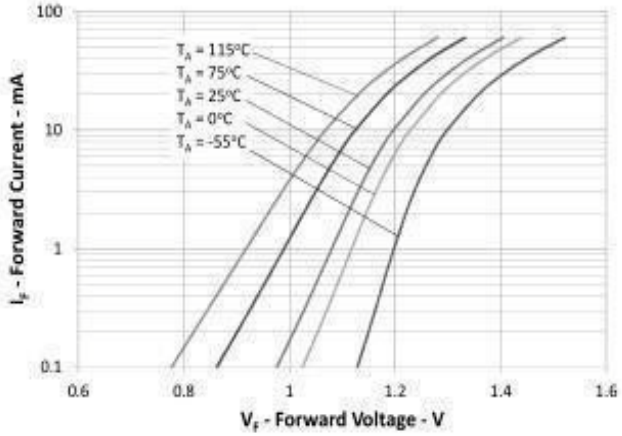


Fig.5 Current Transfer Ratio vs. Forward Current

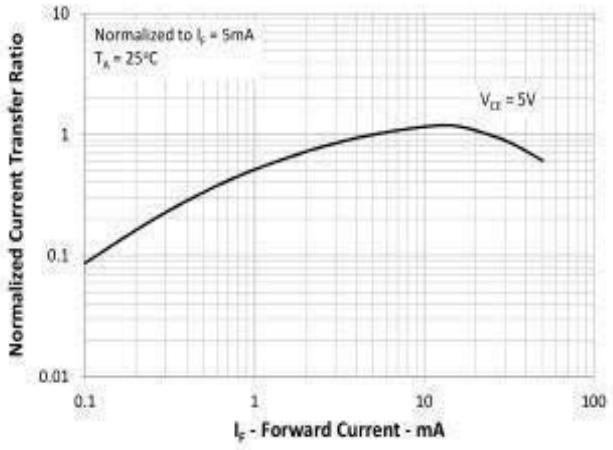


Fig.6 Collector Current vs. Collector-emitter Voltage

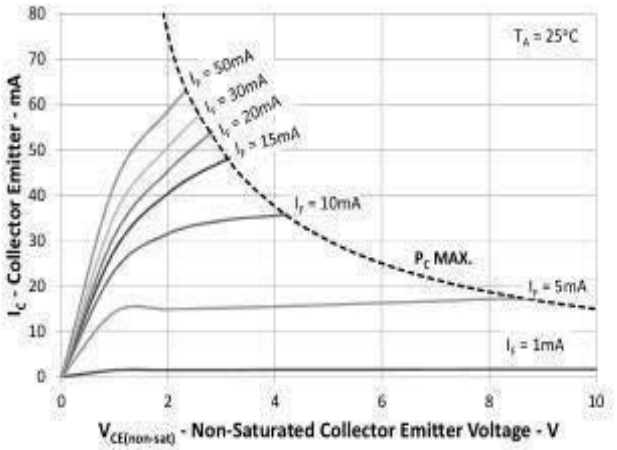


Fig.7 Relative Current Transfer Ratio vs. Ambient Temperature

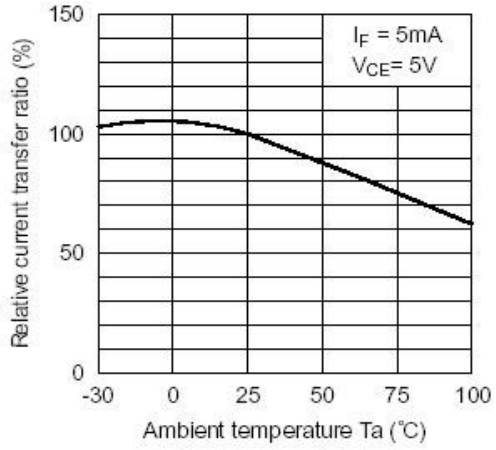


Fig.8 Collector-emitter Saturation Voltage vs. Ambient Temperature

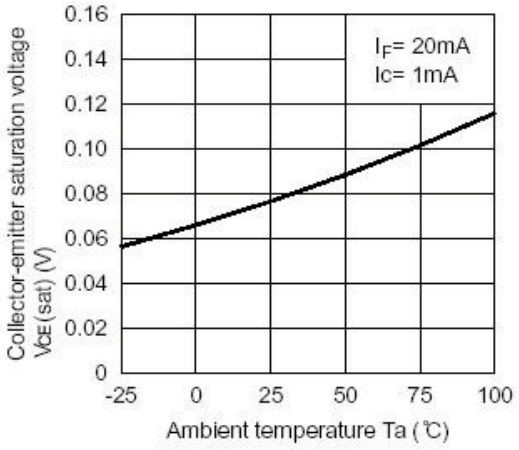


Fig.9 Collector Dark Current vs. Ambient Temperature

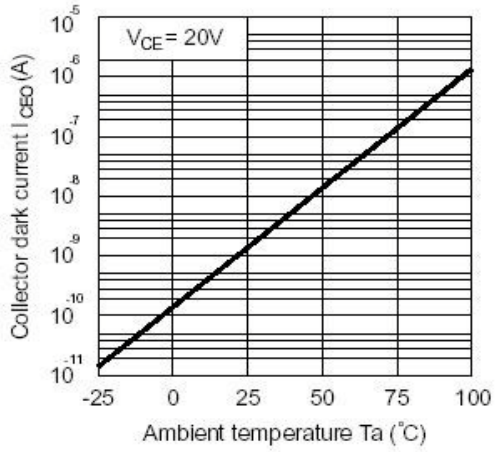


Fig.10 Response Time vs. Load Resistance

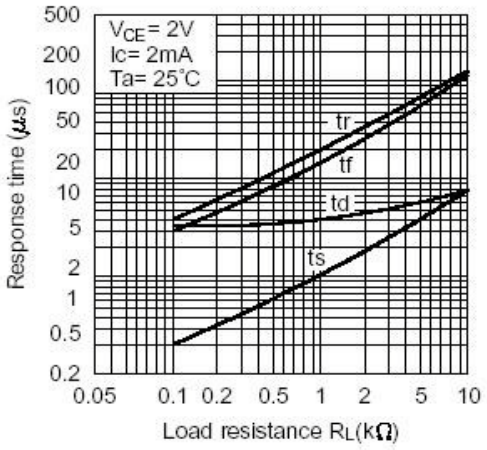
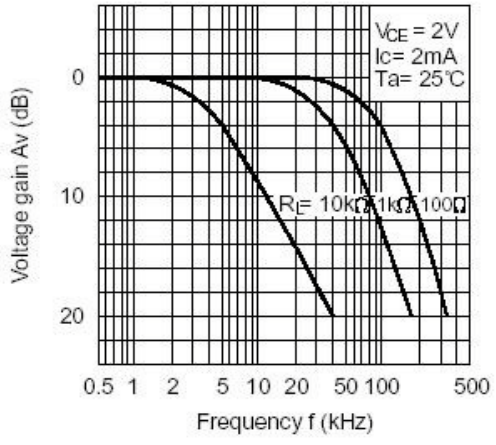
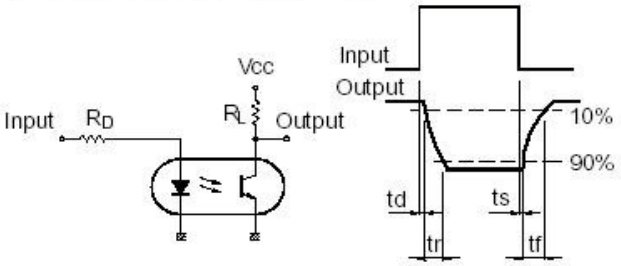


Fig.11 Frequency Response



Test Circuit for Response Time



Test Circuit for Frequency Response